

BUV26 – BUV26A

SILICON POWER TRANSISTORS

High-speed,NPN power transistors in a TO-220 envelope. They are intended for fast switching applications such as high frequency and efficiency converters, switching regulators and motor control.

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value		Unit
			BUV26	BUV26A	
V _{CBO}	Collector-Base Voltage	I _E = 0	180	200	V
V _{CEO}	Collector-Emitter Voltage	I _B = 0	90	100	V
V _{EBO}	Emitter-Base Voltage	I _C = 0	7	5	V
I _C	Collector Current		14		A
I _{CM}	Collector Peak Current	t _p = 10ms	25		A
I _B	Base Current		4		A
I _{BM}	Base Current	t _p = 10ms	6		A
P _t	Power Dissipation		85	65	W
T _j	Junction Temperature		150		°C
T _{stg}	Storage Temperature range		-65 to 150		

Limiting values in accordance with the Absolute Maximum System (IEC 134)

THERMAL CHARACTERISTICS

Symbol	Ratings		Value	Unit
R_{thJ-mb}	From junction to mounting base	BUV26	1.76	°C/W
		BUV26A		

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Value			Unit
			Min	Typ	Max	
I_{CEX}	Collector Cutoff Current (*)	$V_{CE} = V_{CESMax}$ $V_{BE} = 1.5V, T_J = 125^\circ C$	-	-	1	mA
		BUV26 BUV26A				
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 5V, I_C = 0$	-	-	1	mA
		BUV26 BUV26A				
$V_{CE0sust}$	Collector-Emitter Sustaining Voltage	$I_B = 0, I_C = 0.2A$ $L = 25mH$	90	-	-	V
		BUV26 BUV26A	100	-	-	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage	$I_C = 6A, I_B = 600mA$	BUV26	-	-	V
		$I_C = 5A, I_B = 500mA$	BUV26A	-	-	
		$I_C = 12A, I_B = 1.2A$	BUV26	-	-	
		$I_C = 10A, I_B = 1A$	BUV26A	-	-	
$V_{BE(SAT)}$	Base-Emitter Saturation Voltage	$I_C = 6A, I_B = 600mA$	BUV26	-	-	V
		$I_C = 5A, I_B = 500mA$	BUV26A	-	-	
		$I_C = 12A, I_B = 1.2A$	BUV26	-	-	
		$I_C = 10A, I_B = 1A$	BUV26A	-	-	

SWITCHING TIMES

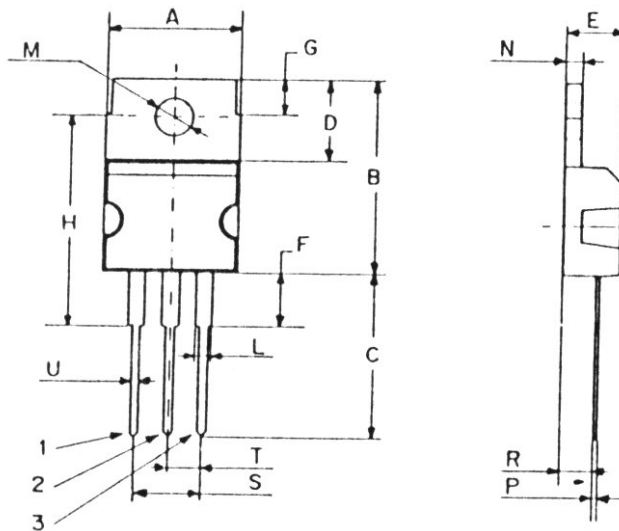
Symbol	Ratings	Test Condition(s)		Value			Unit
				Min	Typ	Max	
t _{on}	turn-on time	For BUV26 I _C = 12 A , V _{CC} = 50 V I _{B1} = 1.2 A , I _{B2} = 2 A	BUV26	-	0.4	0.8	μs
			BUV26A				
t _{off}	turn-off time	For BUV26A	BUV26	-	0.5	1.2	
			BUV26A				
t _f	Fall time	I _C = 10 A , V _{CC} = 50 V I _{B1} = 1 A , I _{B2} = 2 A	BUV26	-	0.12	0.4	
			BUV26A				

(*) Measured with a half-sinewave voltage (curve tracer).

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MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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